

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 1-30. (Canceled).

31. (Original) A method for controlling rippling caused by optical proximity correction during an optical lithography process used in manufacturing an integrated circuit, comprising:

- selecting a first evaluation point for a given segment that is part of an edge in a layout of the integrated circuit;
- selecting a second evaluation point for the given segment;
- computing a first deviation from a target location for the given segment at the first evaluation point;
- computing a second deviation for the given segment at the second evaluation point; and
- adjusting a bias for the given segment, if necessary, based upon multiple deviations at multiple evaluation points, including the first deviation at the first evaluation point and the second deviation at the second evaluation point.

1 32. (Original) The method of claim 31, wherein the second evaluation
2 point is a supplemental evaluation point.

1 33. (Original) The method of claim 31, wherein both the first evaluation
2 point and the second evaluation point are located on the given segment.

1 34. (Original) The method of claim 31, wherein the first evaluation point
2 is located on the given segment and the second evaluation point is located on an
3 adjacent segment.

1 35. (Original) The method of claim 31, further comprising adjusting the
2 bias, if necessary, for each segment that is part of the layout of the integrated
3 circuit.

1 36. (Original) The method of claim 31, further comprising:
2 selecting a third evaluation point for the given segment; and
3 computing a third deviation for the given segment at the third evaluation
4 point;
5 wherein adjusting the bias for the given segment involves considering the
6 third deviation at the third evaluation point.

1 37. (Original) The method of claim 31, wherein computing the first
2 deviation involves using a model-based technique for computing the first
3 deviation.

1 38. (Original) A computer-readable storage medium storing instructions
2 that when executed by a computer cause the computer to perform a method for
3 controlling rippling caused by optical proximity correction during an optical
4 lithography process used in manufacturing an integrated circuit, the method
5 comprising:
6 selecting a first evaluation point for a given segment that is part of an edge
7 in a layout of the integrated circuit;
8 selecting a second evaluation point for the given segment;

9 computing a first deviation from a target location for the given segment at
10 the first evaluation point;
11 computing a second deviation for the given segment at the second
12 evaluation point; and
13 adjusting a bias for the given segment, if necessary, based upon multiple
14 deviations at multiple evaluation points, including the first deviation at the first
15 evaluation point and the second deviation at the second evaluation point.

1 39. (Original) The computer-readable storage medium of claim 38,
2 wherein the second evaluation point is a supplemental evaluation point.

1 40. (Original) The computer-readable storage medium of claim 38,
2 wherein both the first evaluation point and the second evaluation point are located
3 on the given segment.

1 41. (Original) The computer-readable storage medium of claim 38,
2 wherein the first evaluation point is located on the given segment and the second
3 evaluation point is located on an adjacent segment.

1 42. (Original) The computer-readable storage medium of claim 38,
2 wherein the method further comprises adjusting the bias, if necessary, for each
3 segment that is part of the layout of the integrated circuit.

1 43. (Original) The computer-readable storage medium of claim 38,
2 wherein the method further comprises:
3 selecting a third evaluation point for the given segment; and
4 computing a third deviation for the given segment at the third evaluation
5 point;

1 47. (Original) The apparatus of claim 45, wherein both the first evaluation
2 point and the second evaluation point are located on the given segment.

1 48. (Original) The apparatus of claim 45, wherein the first evaluation point
2 is located on the given segment and the second evaluation point is located on an
3 adjacent segment.

1 49. (Original) The apparatus of claim 45, wherein the bias adjustment
2 mechanism is configured to adjust the bias, if necessary, for each segment that is
3 part of the layout of the integrated circuit.

1 50. (Original) The apparatus of claim 45,
2 wherein the selection mechanism is additionally configured to select a
3 third evaluation point for the given segment; and
4 wherein the deviation computing mechanism is additionally configured to
5 compute a third deviation for the given segment at the third evaluation point;
6 wherein the bias adjustment mechanism is configured to consider the third
7 deviation at the third evaluation point in adjusting the bias for the given segment
8 involves.

1 51. (Original) The apparatus of claim 45, wherein the deviation computing
2 mechanism is configured to compute use a model-based technique in computing
3 the first deviation.

1 52. (Original) A mask to be used in an optical lithography process for
2 manufacturing an integrated circuit, wherein the mask is created through a process
3 that controls rippling caused by optical proximity correction, the process
4 comprising:

5 selecting a first evaluation point for a given segment that is part of an edge
6 in a layout of the integrated circuit;
7 selecting a second evaluation point for the given segment;
8 computing a first deviation from a target location for the given segment at
9 the first evaluation point;
10 computing a second deviation for the given segment at the second
11 evaluation point; and
12 adjusting a bias for the given segment, if necessary, based upon multiple
13 deviations at multiple evaluation points, including the first deviation at the first
14 evaluation point and the second deviation at the second evaluation point.

1 53. (Original) An integrated circuit created through a process that controls
2 rippling caused by optical proximity correction during an optical lithography
3 process used in manufacturing the integrated circuit, the process comprising:
4 selecting a first evaluation point for a given segment that is part of an edge
5 in a layout of the integrated circuit;
6 selecting a second evaluation point for the given segment;
7 computing a first deviation from a target location for the given segment at
8 the first evaluation point;
9 computing a second deviation for the given segment at the second
10 evaluation point; and
11 adjusting a bias for the given segment, if necessary, based upon multiple
12 deviations at multiple evaluation points, including the first deviation at the first
13 evaluation point and the second deviation at the second evaluation point.

1 54. (Original) A means for controlling rippling caused by optical
2 proximity correction during an optical lithography process used in manufacturing
3 an integrated circuit, comprising:

4 a selection means for,
5 selecting a first evaluation point for a given segment that is
6 part of an edge in a layout of the integrated circuit, and for
7 selecting a second evaluation point for the given segment;
8 a deviation computing means for,
9 computing a first deviation from a target location for the
10 given segment at the first evaluation point, and for
11 computing a second deviation for the given segment at the
12 second evaluation point; and
13 a bias adjustment means for adjusting a bias for the given segment, if
14 necessary, based upon multiple deviations at multiple evaluation points, including
15 the first deviation at the first evaluation point and the second deviation at the
16 second evaluation point.